New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

Silicon NPN Power Transistors — 2N6537

DESCRIPTION

·With TO-66 package
·DARLINGTON

APPLICATIONS

·Power switching
·Hammer drivers
·Series and shunt regulators
·Audio amplifiers

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

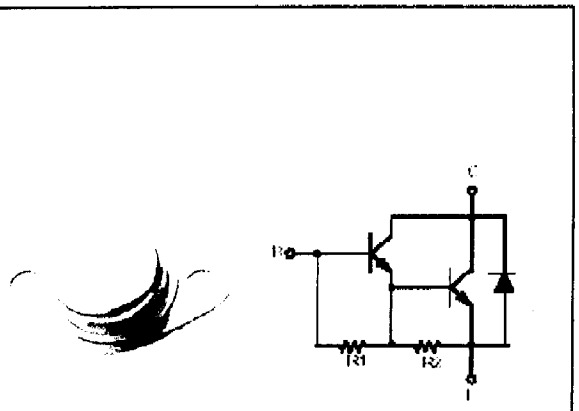

Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	120	V
V_{CEO}	Collector-emitter voltage	Open base	120	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		8	A
I_{CM}	Collector current-Peak		15	A
I_B	Base current		0.25	A
P_T	Total power dissipation	T_C=25□	36	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.2A ; I_B=0	120			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	I_C=3A ; I_B=6mA			2.0	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	I_C=8A; I_B=80mA			3.0	V
V_{BE-1}	Base -emitter on voltage	I_C=3A ; V_{CE}=3V			2.8	V
V_{BE-2}	Base -emitter on voltage	I_C=8A ; V_{CE}=3V			4.5	V
I_{CEV}	Collector cut-off current	V_{CE}=120V; V_{BE}=-1.5V T_C=125□			0.5 5.0	mA
I_{CEO}	Collector cut-off current	V_{CE}=120V; I_B=0			1.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			5.0	mA
h_{FE-1}	DC current gain	I_C=3A ; V_{CE}=3V	1000		10000	
h_{FE-2}	DC current gain	I_C=8A ; V_{CE}=3V	100		5000	
V_F	Diode forward voltage	I_F=5A			4.0	V